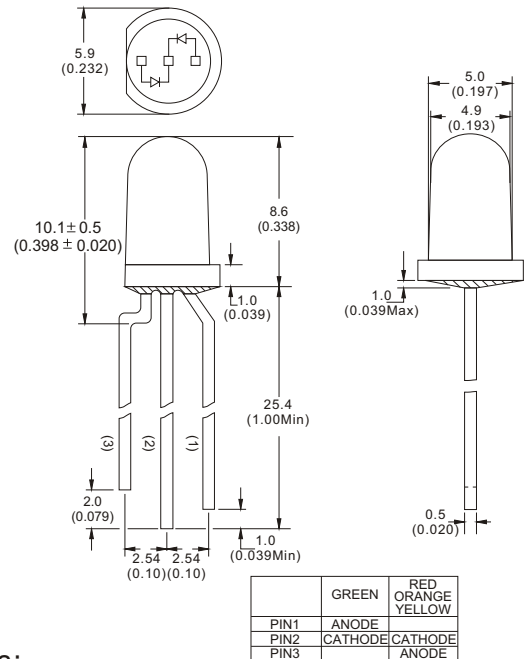




● Features:

- 1. Chip material: GaAsP+GaP
- 2. Emitting color: Orange/Green
- 3. Lens Appearance: White Diffused
- 4. Long life-solid state reliability
- 5. IC compatible/Low current capability
- 6. RoHS compliant

● Package dimensions



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is ±0.25mm (0.01") unless otherwise specified.
- 3. Specifications are subject to change without notice.



● Absolute maximum ratings (Ta=25°C)

Characteristic	Test Condition	Symbol	E	G	Units
Pulse Forward Current	1/10 duty cycle 0.1ms Pulse width	I _{FP}	100	100	mA
DC Forward Current		I _F	25	25	mA
Reverse Current	V _R =5V	I _R	10	10	μA
Power Dissipation		P _D	65	80	mW
Operating Temperature		T _{OPR}	-40 to +80		°C
Storage Temperature		T _{STG}	-40 to +85		°C
Lead Soldering Temperature	1.60mm from body maximum 3 seconds	T _{SOL}	260		°C

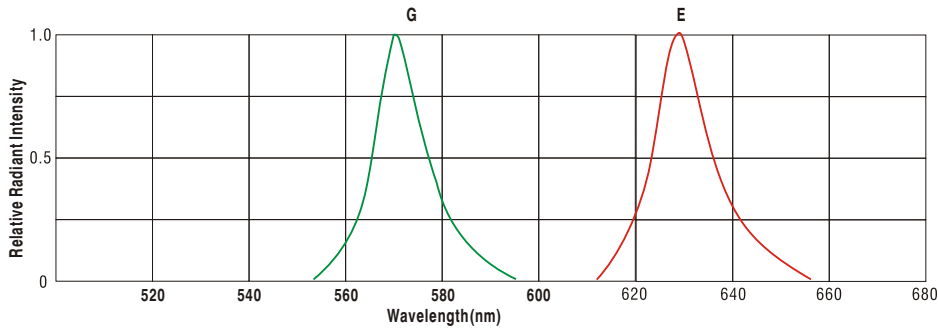


● Electrical And Optical Characteristics(Ta=25°C)

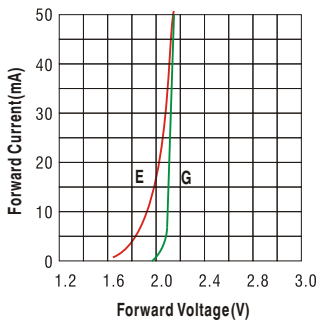
Parameter	Test Condition	Symbol	Colors	Typ.	Max.	Units
Forward Voltage	IF=20mA	V _F	E	2.10	2.50	V
Reverse Current	V _R =5V	I _R		---	10	μA
Peak Wavelength	IF=20mA	λ _P		632	---	nm
Dominant Wavelength	IF=20mA	λ _D		624	---	nm
Spectral Line Half-width	IF=20mA	Δλ		35	---	nm
Luminous Intensity	IF=20mA	I _V		20	---	mcd
Forward Voltage	IF=20mA	V _F	G	2.20	2.50	V
Reverse Current	V _R =5V	I _R		---	10	μA
Peak Wavelength	IF=20mA	λ _P		568	---	nm
Dominant Wavelength	IF=20mA	λ _D		565	---	nm
Spectral Line Half-width	IF=20mA	Δλ		30	---	nm
Luminous Intensity	IF=20mA	I _V		15	---	mcd
Viewing Angle	IF=20mA	2θ½	EG	60	---	deg.

● Typical electro-optical characteristics curves

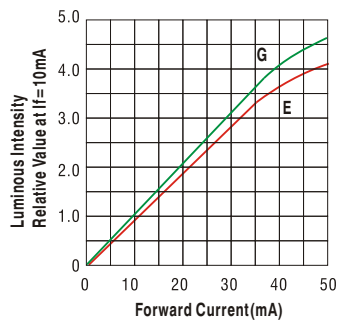
RELATIVE INTENSITY VS WAVELENGTH



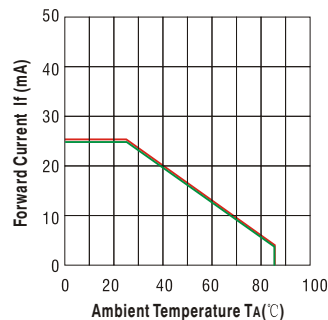
FORWARD CURRENT VS FORWARD VOLTAGE



LUMINOUS INTENSITY VS FORWARD CURRENT



FORWARD CURRENT DERATING CURVE



LUMINOUS INTENSITY VS AMBIENT TEMPERATURE

